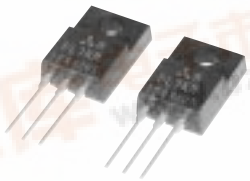
MITSUBISHI Nch POWER MOSFET

FL7KM-12A

PRELIMINARY
Notice: This is not a final specification.
Some parametric limits are subject to change.

HIGH-SPEED SWITCHING USE

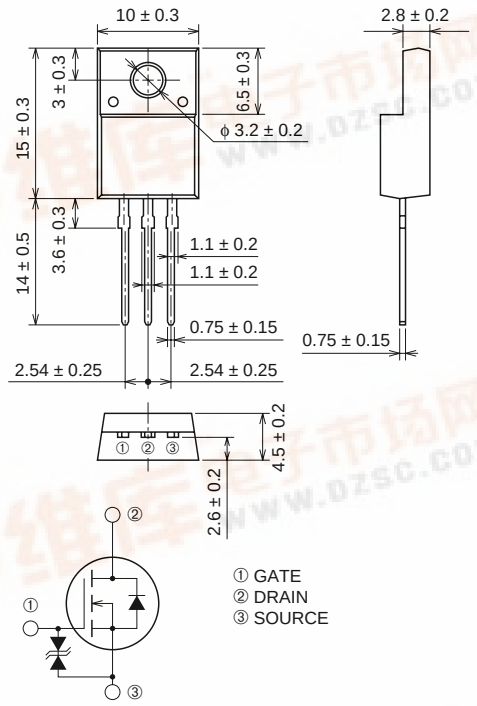
FL7KM-12A



- 10V DRIVE
- VDSS 600V
- rDS (ON) (MAX) 1.3Ω
- ID 7A

OUTLINE DRAWING

Dimensions in mm



TO-220FN

APPLICATION

Switch mode power supply, Inverter fluorescent lamp, etc.

MAXIMUM RATINGS (Tc = 25°C)

Symbol	Parameter	Conditions	Ratings	Unit
VDSS	Drain-source voltage	VGS = 0V	600	V
VGSS	Gate-source voltage	VDS = 0V	±30	V
ID	Drain current		7	A
IDM	Drain current (Pulsed)		21	A
IDA	Avalanche drain current (Pulsed)	L = 200µH	7	A
PD	Maximum power dissipation		35	W
Tch	Channel temperature		–55 ~ +150	°C
Tstg	Storage temperature		–55 ~ +150	°C
Viso	Isolation voltage	AC for 1minute, Terminal to case	2000	V
—	Weight	Typical value	2.0	g

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FL7KM-12A

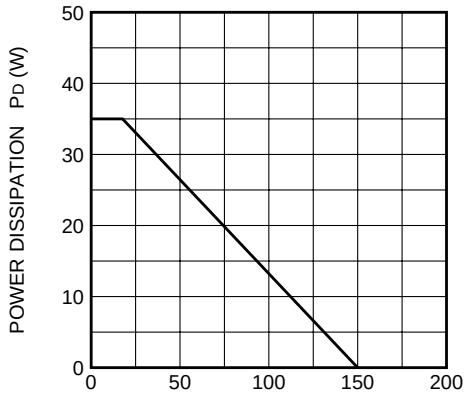
HIGH-SPEED SWITCHING USE

ELECTRICAL CHARACTERISTICS (Tch = 25°C)

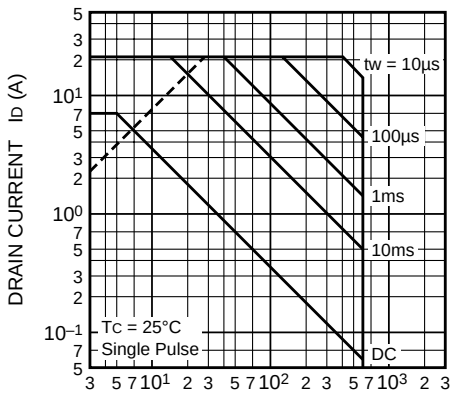
Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
$V_{(BR)\ DSS}$	Drain-source breakdown voltage	I_D = 1mA, V_{GS} = 0V	600	—	—	V
$V_{(BR)\ GSS}$	Gate-source breakdown voltage	I_{GS} = ±100μA, V_{DS} = 0V	±30			V
I_{GSS}	Gate-source leakage current	V_{GS} = ±25V, V_{DS} = 0V	—	—	±10	μA
I_{DSS}	Drain-source leakage current	V_{DS} = 600V, V_{GS} = 0V	—	—	1	mA
$V_{GS\ (th)}$	Gate-source threshold voltage	I_D = 1mA, V_{DS} = 10V	2.0	3.0	4.0	V
$r_{DS\ (ON)}$	Drain-source on-state resistance	I_D = 3A, V_{GS} = 10V	—	1.1	1.3	Ω
$V_{DS\ (ON)}$	Drain-source on-state voltage	I_D = 3A, V_{GS} = 10V	—	3.3	3.9	V
$\lvert y_{fs} \rvert$	Forward transfer admittance	I_D = 3A, V_{DS} = 10V	—	5.0	—	S
C_{iss}	Input capacitance	V_{DS} = 25V, V_{GS} = 0V, f = 1MHz	—	950	—	pF
C_{oss}	Output capacitance		—	115	—	pF
C_{rss}	Reverse transfer capacitance		—	30	—	pF
$t_{d\ (on)}$	Turn-on delay time	V_{DD} = 200V, I_D = 3A, V_{GS} = 10V, R_{GEN} = R_{GS} = 50Ω	—	20	—	ns
t_r	Rise time		—	30	—	ns
$t_{d\ (off)}$	Turn-off delay time		—	180	—	ns
t_f	Fall time		—	65	—	ns
V_{SD}	Source-drain voltage	I_S = 3A, V_{GS} = 0V	—	1.5	2.0	V
$R_{th\ (ch-c)}$	Thermal resistance	Channel to case	—	—	3.57	°C/W

PERFORMANCE CURVES

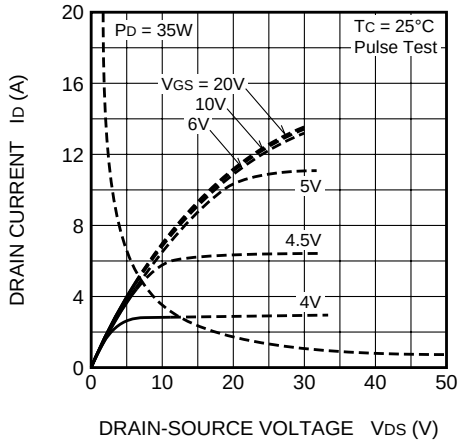
POWER DISSIPATION DERATING CURVE



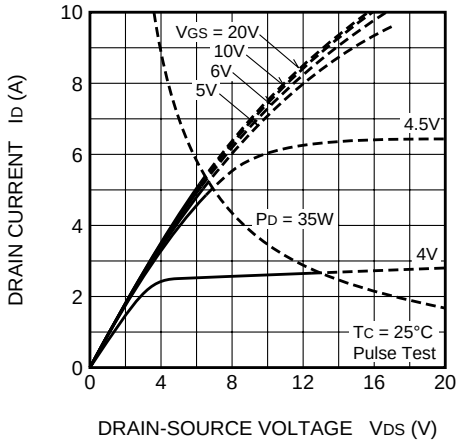
MAXIMUM SAFE OPERATING AREA



OUTPUT CHARACTERISTICS (TYPICAL)

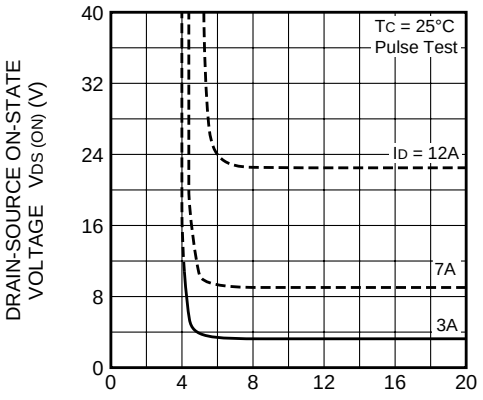


OUTPUT CHARACTERISTICS (TYPICAL)

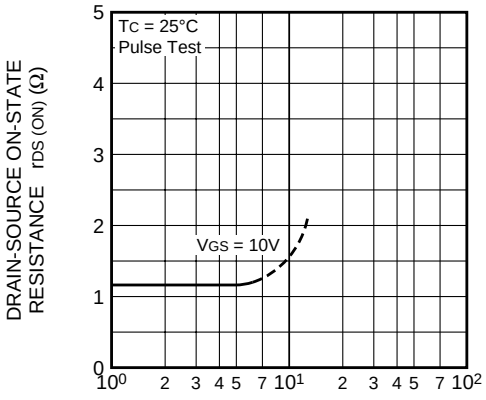


MITSUBISHI ELECTRIC

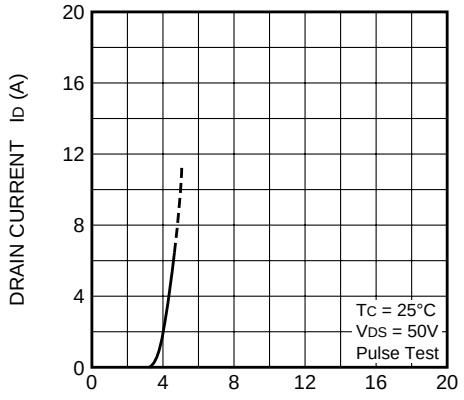
ON-STATE VOLTAGE VS. GATE-SOURCE VOLTAGE (TYPICAL)



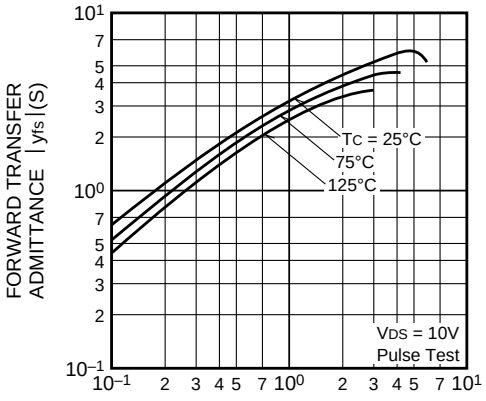
ON-STATE RESISTANCE VS. DRAIN CURRENT (TYPICAL)



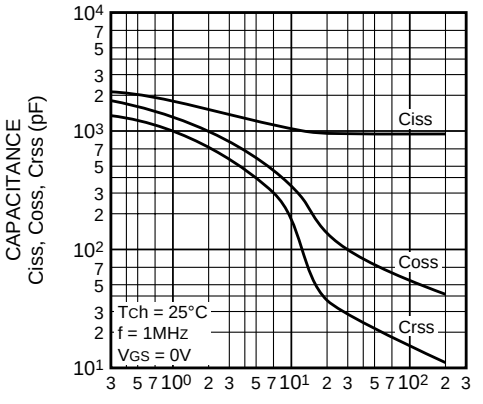
TRANSFER CHARACTERISTICS (TYPICAL)



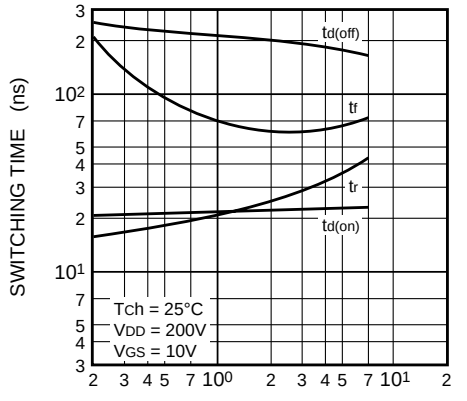
FORWARD TRANSFER ADMITTANCE VS. DRAIN CURRENT (TYPICAL)



CAPACITANCE VS. DRAIN-SOURCE VOLTAGE (TYPICAL)



SWITCHING CHARACTERISTICS (TYPICAL)



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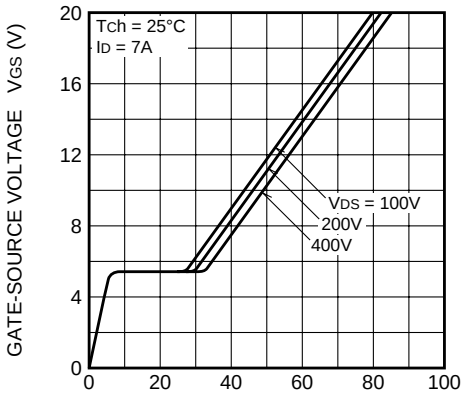
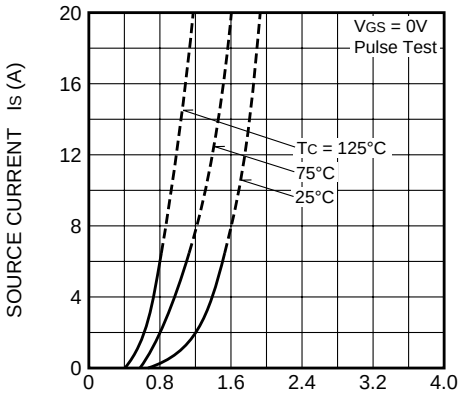
FL7KM-12A

HIGH-SPEED SWITCHING USE

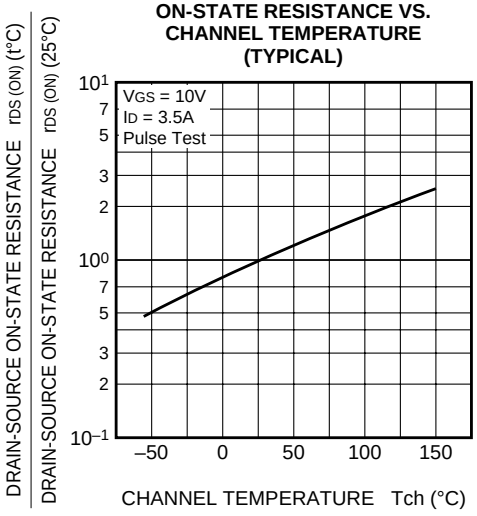
GATE-SOURCE VOLTAGE VS. GATE CHARGE (TYPICAL)



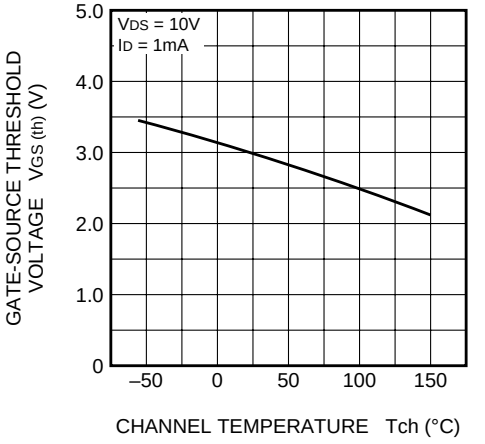
SOURCE-DRAIN DIODE FORWARD CHARACTERISTICS (TYPICAL)



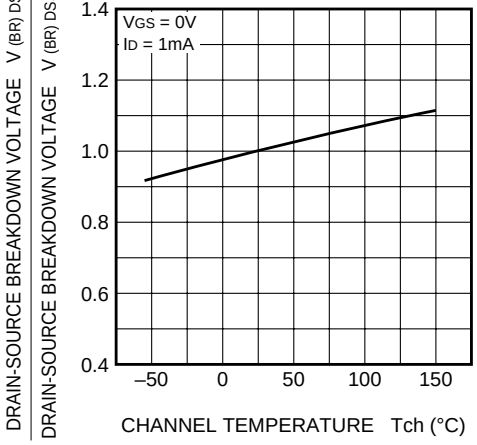
ON-STATE RESISTANCE VS. CHANNEL TEMPERATURE (TYPICAL)



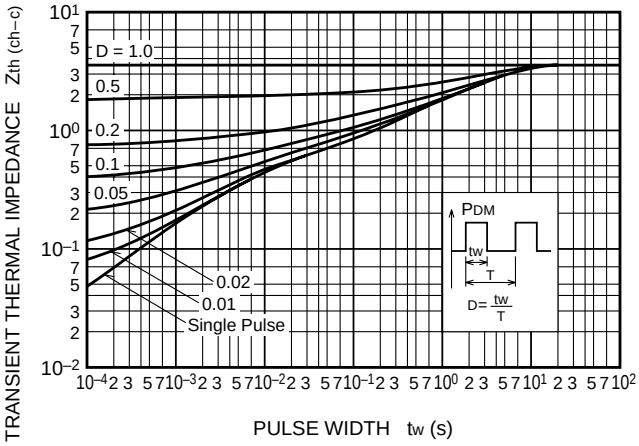
THRESHOLD VOLTAGE VS. CHANNEL TEMPERATURE (TYPICAL)



BREAKDOWN VOLTAGE VS. CHANNEL TEMPERATURE (TYPICAL)



TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS



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